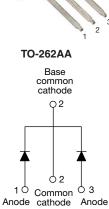
www.vishay.com

VS-20CTH03SHM3, VS-20CTH03-1HM3

Vishay Semiconductors







Common Anode cathode Anode VS-20CTH03SHM3

10

2

03

02

VS-20CTH03-1HM3

PRIMARY CHARACTERISTICS								
I _{F(AV)}	2 x 10 A							
V _R	300 V							
V _F at I _F	0.85 V							
t _{rr} typ.	23 ns							
T _J max.	175 °C							
Package	TO-263AB (D ² PAK), TO-262AA							
Circuit configuration Common cathode								

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum COMPLIANT HALOGEN peak of 260 °C FREE



- AEC-Q101 qualified, meets JESD 201, class 1 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Peak repetitive reverse voltage		V _{RRM}		300	V				
Average rectified forward current	per diode	I _{F(AV)}	T _C = 160 °C	10					
	per device			20	A				
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	120					
Operating junction and storage temperatures		T _J , T _{Stg}		-55 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)										
PARAMETER	MIN.	TYP.	MAX.	UNITS						
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	300	-	-					
E	V _F	I _F = 10 A	-	1.05	1.25	, V				
Forward voltage		I _F = 10 A, T _J = 125 °C	-	0.85	0.95	l				
Povoroo lookago ourront		$V_R = V_R$ rated	-	-	20					
Reverse leakage current	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	6	200	μA				
Junction capacitance	CT	V _R = 300 V	-	30	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH				

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Document Number: 95671

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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	100 A/ μ s, V _R = 30 V	-	23	-				
Reverse recovery time	t _{rr}	T _J = 25 °C		-	31	-	ns			
		T _J = 125 °C		-	42	-				
Pools receivers ourrent	I _{RRM}	T _J = 25 °C	$I_F = 10 A$	-	2.4	-	A nC			
Peak recovery current		T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 200 V	-	5.6	-				
Reverse recovery charge	0	T _J = 25 °C		-	36	-				
neverse recovery charge	Q _{rr}	T _J = 125 °C		_	120	_				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Thermal resistance, junction to case per diode	R _{thJC}		-	-	1.5	°C/W				
Weight			-	2.0	-	g				
Weight			-	0.07	-	oz.				
Marking davias		Case style TO-263AB (D ² PAK)	20CTH03SH							
Marking device		Case style TO-262AA	20CTH03-1H							

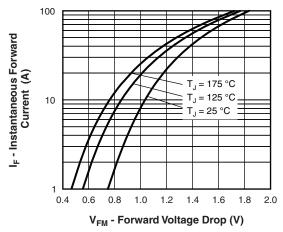


Fig. 1 - Maximum Forward Voltage Drop Characteristics

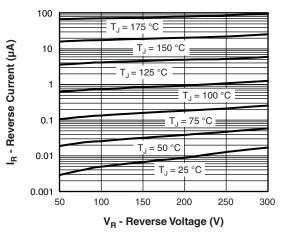


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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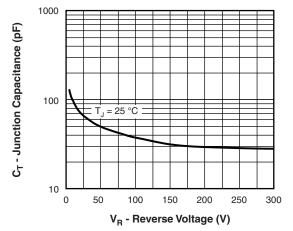


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

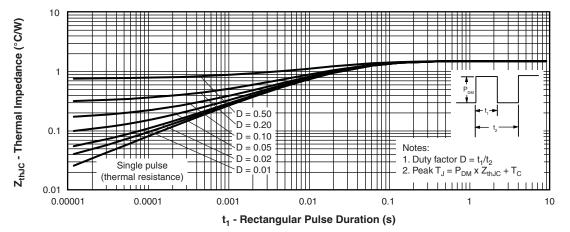
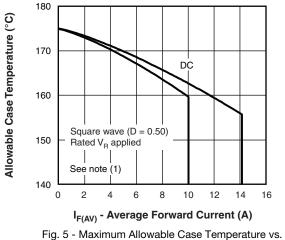
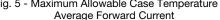
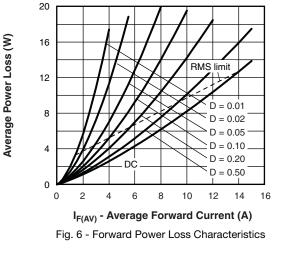


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics







Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V_{\mathsf{FM}}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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3

Document Number: 95671

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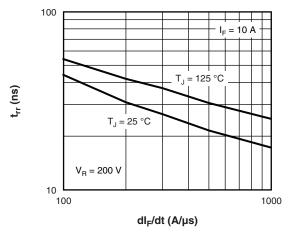


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

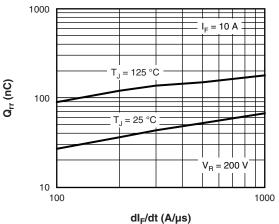


Fig. 8 - Typical Stored Charge vs. dl_F/dt

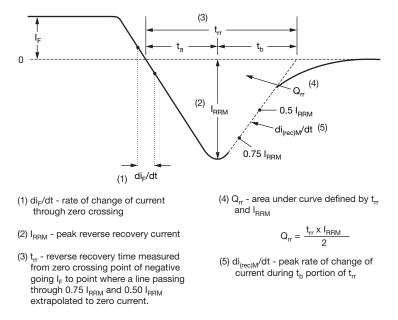
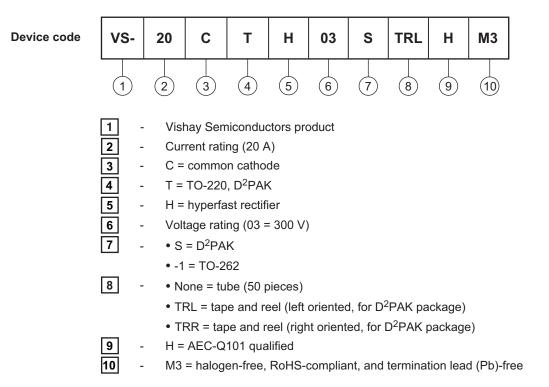


Fig. 9 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE



LINKS TO RELATED DOCUMENTS								
Dimensions	TO-263AB (D ² PAK)	www.vishay.com/doc?95046						
	TO-262AA	www.vishay.com/doc?95419						
	TO-263AB (D ² PAK)	www.vishay.com/doc?95444						
Part marking information	TO-262AA	www.vishay.com/doc?95443						
Packaging information	TO-263AB (D ² PAK)	www.vishay.com/doc?95032						
SPICE model		www.vishay.com/doc?96583						

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

www.vishay.com

SHA



SYMBOL	SYMBOL MILLIMETERS		LLIMETERS INCI		INCHES NOTES		SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	IE3	STMBOL	MIN.	MAX.	MIN.	MAX.	NUTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 08-Jul-15

1

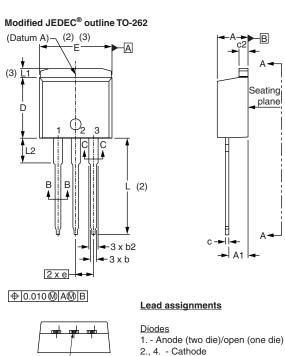
Outline Dimensions



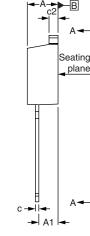
Vishay Semiconductors

TO-262

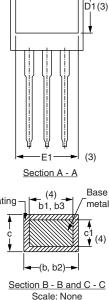
DIMENSIONS in millimeters and inches



Lead tip -



E1 Plating



Е

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. А 4.06 4.83 0.160 0.190 2.03 A1 3.02 0.080 0.119 b 0.51 0.99 0.020 0.039 b1 0.51 0.89 0.020 0.035 4 b2 1.14 1.78 0.045 0.070 1.14 1.73 0.045 0.068 4 b3 0.38 0.74 0.015 0.029 С 0.38 0.58 0.015 0.023 4 c1 1.14 1.65 0.045 0.065 c2 D 8.51 9.65 0.335 0.380 2 D1 6.86 8.00 0.270 0.315 3 Е 9.65 10.67 0.380 0.420 2, 3 E1 7.90 8.80 0.311 0.346 3 0.100 BSC 2.54 BSC е L 13.46 14.10 0.530 0.555 L1 _ 1.65 0.065 3 _ 3.36 0.132 0.146 L2 3.71

3. - Anode

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC TO-262 except A1 (maximum), (6) b (minimum), D1 (minimum) and L2 where dimensions derived the actual package outline

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Document Number: 95419

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